

Dual N-channel 80 V, 30 mΩ logic level MOSFET 17 August 2017

Product data sheet

1. General description

Dual Logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- Repetitive avalanche rated •
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 $^\circ\text{C}$

3. Applications

- 12 V, 24 V and 48 V automotive systems •
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick	reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Limiting value	es FET1 and FET2	·				,
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	17	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	53	W
Static charact	eristics FET1 and FET2	·				
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	21	30	mΩ
Dynamic char	acteristics FET1 and FE	T2				
Q _{GD}	gate-drain charge	$\begin{split} I_D &= 5 \text{ A}; \text{V}_{DS} = 64 \text{V}; \text{V}_{GS} = 5 \text{V}; \\ T_j &= 25 ^\circ\text{C}; \overline{\text{Fig. 13}}; \overline{\text{Fig. 14}} \end{split}$	-	6.2	-	nC

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5. Pinning information

Table 2. I	Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	S1	source1	8 7 6 5	D1 D1 D2 D2				
2	G1	gate1						
3	S2	source2						
4	G2	gate2						
5	D2	drain2		S1 $G1$ $S2$ $G2$				
6	D2	drain2		mbk725				
7	D1	drain1						
8	D1	drain1	LFPAK56D (SOT1205)					

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK9K30-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads; 1.27 mm pitch; 4.7 mm x 5.3 mm x 1.05 mm body	SOT1205				

7. Marking

Table 4. Marking codes					
Type number	Marking code				
BUK9K30-80E	93080E				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Limiting val	ues FET1 and FET2					
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; $T_j \le 175 \degree C$	[1] [2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	53	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	17	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	12	А

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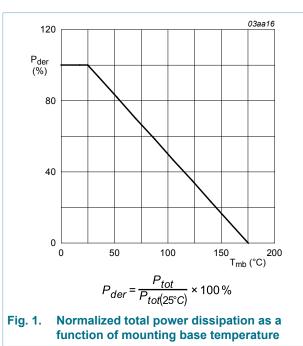
Symbol	Parameter	Conditions		Min	Max	Unit
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	68	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode FET1 and FET2		·			
ls	source current	T _{mb} = 25 °C		-	17	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	68	А
Avalanche r	uggedness FET1 and FET2		·			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:I_star} \begin{array}{l} I_D = 17 \text{ A}; \ V_{sup} \leq \ 80 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 4 \end{array}$	[3] [4]	-	72	mJ

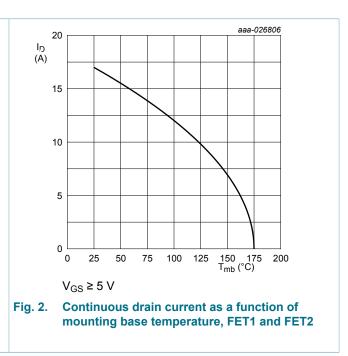
[1] [2] Accumulated Pulse duration up to 50 hours delivers zero defect ppm.

Significantly longer life times are achieved by lowering T_j and or V_{GS} .

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]

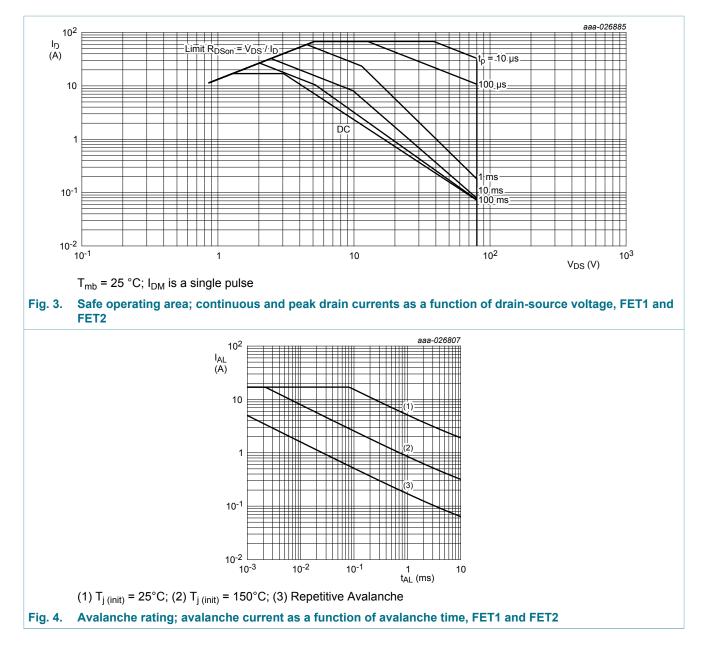
[4] Refer to application note AN10273 for further information.





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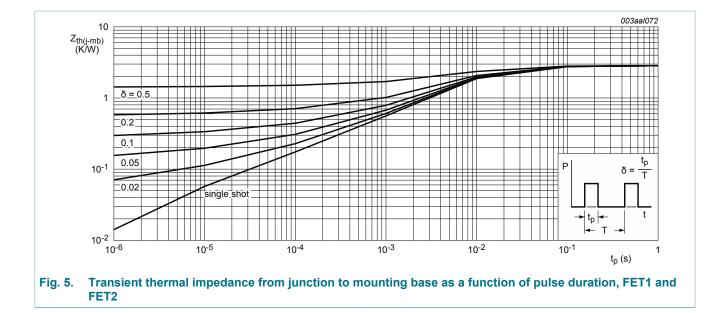


9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.84	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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10. Characteristics

Table 7. Characteristics Symbol Parameter Conditions Min Тур Max Unit Static characteristics FET1 and FET2 drain-source I_D = 250 μA; V_{GS} = 0 V; T_i = 25 °C 80 V V_{(BR)DSS} _ _ breakdown voltage I_D = 250 μA; V_{GS} = 0 V; T_i = -55 °C 72 V _ _ I_D = 1 mA; V_{DS}=V_{GS}; T_i = 25 °C; <u>Fig. 9</u>; V_{GS(th)} gate-source threshold 1.4 1.7 2.1 V voltage Fig. 10 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = -55 \text{ °C};$ V 2.45 _ -Fig. 10 I_D = 1 mA; V_{DS}=V_{GS}; T_i = 175 °C; 0.5 V _ _ Fig. 10 V_{DS} = 80 V; V_{GS} = 0 V; T_i = 25 °C drain leakage current 0.01 1 μA IDSS _ V_{DS} = 80 V; V_{GS} = 0 V; T_i = 175 °C 500 μA _ V_{GS} = 10 V; V_{DS} = 0 V; T_i = 25 °C 2 gate leakage current 100 nA I_{GSS} _ V_{GS} = -10 V; V_{DS} = 0 V; T_i = 25 °C 2 100 nA _ V_{GS} = 5 V; I_D = 5 A; T_i = 25 °C; <u>Fig. 11</u> drain-source on-state 21 30 mΩ **R**_{DSon} _ resistance V_{GS} = 10 V; I_D = 5 A; T_i = 25 °C; Fig. 11 20 26 mΩ _ V_{GS} = 5 V; I_D = 5 A; T_i = 175 °C; <u>Fig. 12</u> 75 mΩ _ _ **Dynamic characteristics FET1 and FET2** total gate charge $I_D = 5 A$; $V_{DS} = 64 V$; $V_{GS} = 5 V$; 17.5 nC Q_{G(tot)} --T_i = 25 °C; <u>Fig. 13</u>; <u>Fig. 14</u> nC Q_{GS} gate-source charge 3.9 -Q_{GD} 6.2 nC gate-drain charge -_ V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; Ciss input capacitance 1727 2297 pF _ T_i = 25 °C; <u>Fig. 15</u> Coss output capacitance 126 151 pF _

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rss}	reverse transfer capacitance		-	68	93	pF
t _{d(on)}	turn-on delay time	V _{DS} = 60 V; R _L = 12 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C	-	10.4	-	ns
t _r	rise time		-	14.8	-	ns
t _{d(off)}	turn-off delay time		-	24.7	-	ns
t _f	fall time		-	15	-	ns
Source-dra	in diode FET1 and FET2					
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	27.2	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	30.8	-	nC

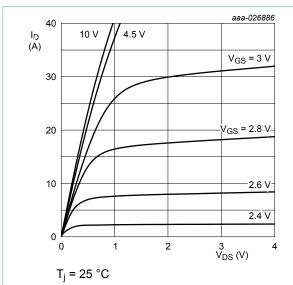


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

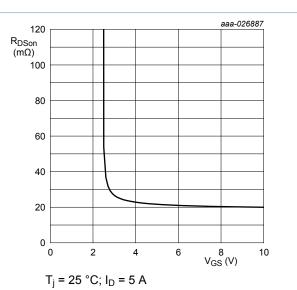
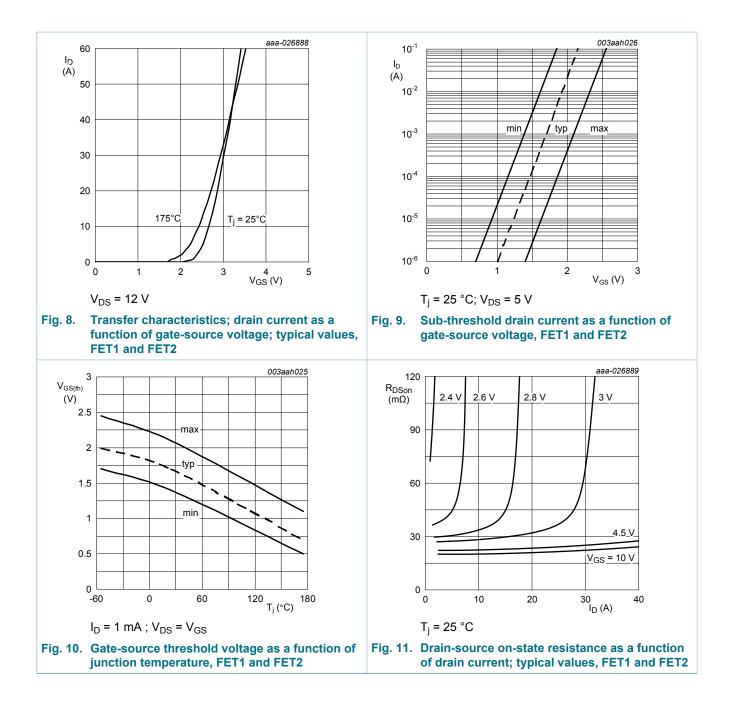


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2

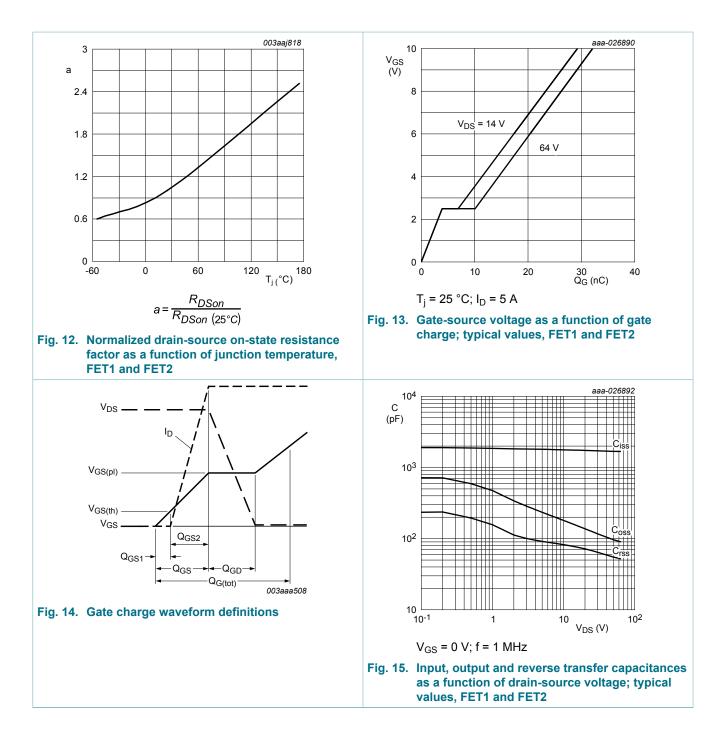
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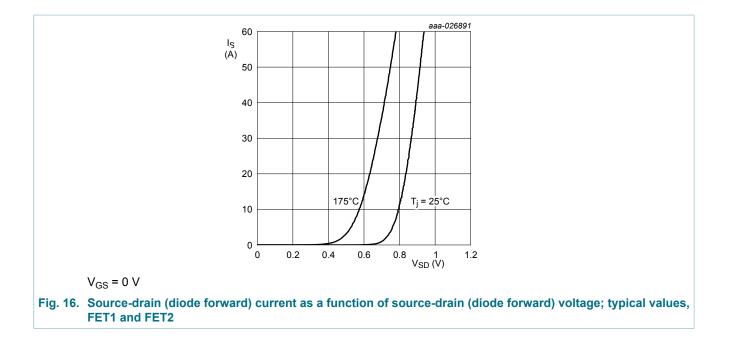
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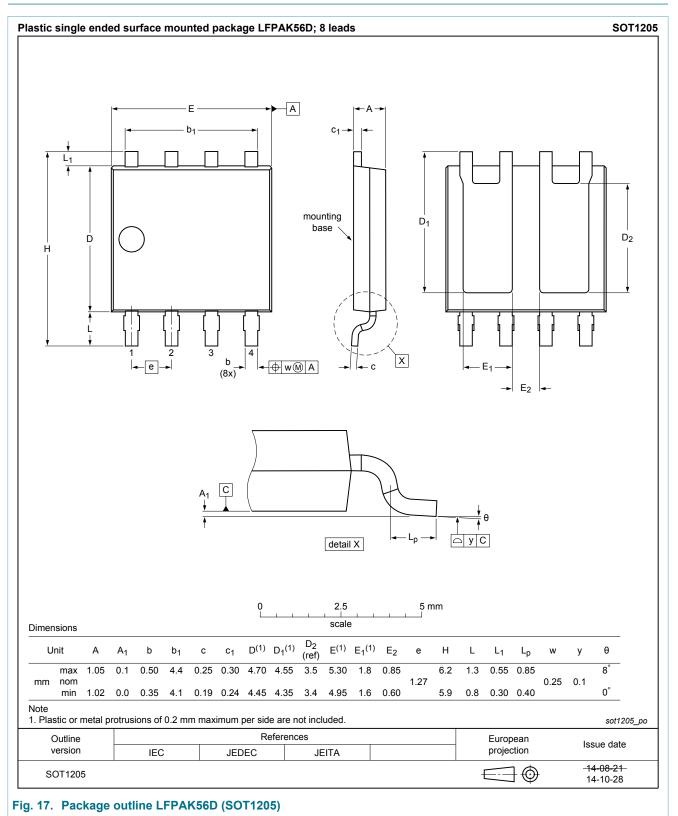
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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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